

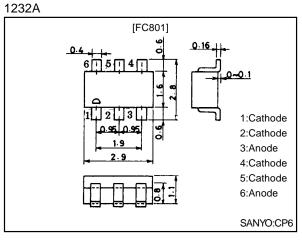
FC801 Silicon Epitaxal Planar Diode Composite Diode for High-Speed Switching Applications

Features

- Composite type with 4 diodes contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC801 is formed with two chips, each being equivalent to the DCA015, placed in one package.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

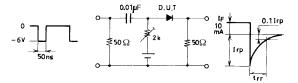
Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V _{RM}		75	V
Reverse Voltage	VR		50	V
Surge Current	IFSM	1µs	4	A
Average Rectified Current	IO		100	mA
Peak Forward Current	IFM		300	mA
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-50 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	٧ _F	I _F =10mA		0.72	1.0	V
		I _F =50mA		0.82	1.0	V
		I _F =100mA		0.88	1.2	V
Reverse Current	IR	V _R =50V			100	nA
Intertermimal Capacitance	С	V _R =0V, f=1MHz		4.5	9.0	pF
Reverse Recovery Time	trr	$I_{F}=10mA$, $V_{R}=6V$, $R_{L}=50\Omega$, $I_{rr}=0.1Irp$			8.0	ns

Note) The specifications shown above are for each individual diode. • Marking:801

Reverse Recovery Time Test Circuit

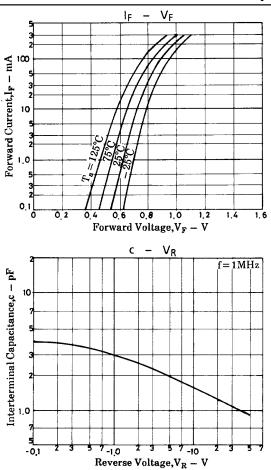


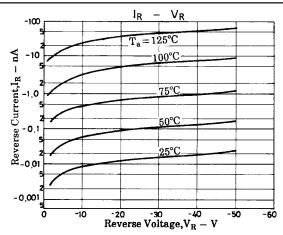
Electrical Connection

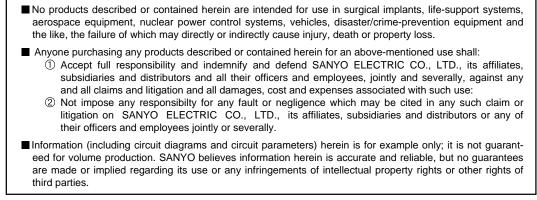


SANYO Electric Co., Ltd. Semiconductor Bussiness Headquarters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

22898HA (KT)/91694MO 8-4998/5169MO, TS No.3107-1/2







This catalog provides information as of February, 1998. Specifications and information herein are subject to change without notice.